NSN 5961-01-160-8703

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View Online at https://aerobasegroup.com/nsn/5961-01-160-8703 **Inclosure Material:** Metal **Overall Length:** 1.421 inches **Overall Height:** 0.450 inches **Overall Width:** 1.050 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: T0-3 **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 375.0 breakdown voltage, collector-to-base, emitter open and 6.0 emitter to base voltage, static, collector open and 300.0 breakdown voltage, collector-to-emitter, base open **Current Rating Per Characteristic:** 5.00 amperes repetitive peak forward current blank and 2.00 amperes repetitive peak forward current **Power Rating Per Characteristic:** 100.0 milliwatts small-signal input power, common-collector **Transfer Ratio:** 80.0 small-signal short-circuit forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Test Data Document:** 02735-66969 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 2 unthreaded hole and 1 case Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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